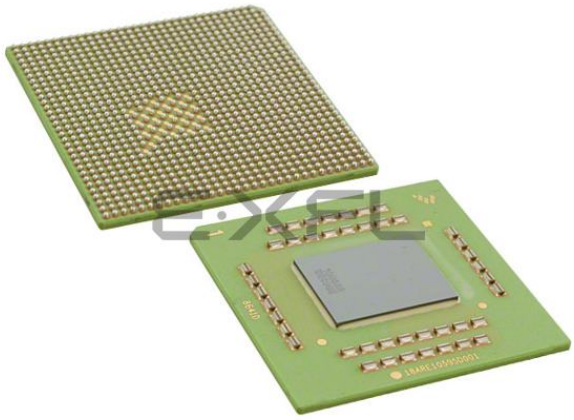

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	PowerPC e600
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	1.333GHz
Co-Processors/DSP	-
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (4)
SATA	-
USB	-
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	994-BCBGA, FCCBGA
Supplier Device Package	994-FCCBGA (33x33)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mc8641vu1333jc

  - Support for PCI-Express message-shared interrupts (MSIs)
- Local bus controller (LBC)
  - Multiplexed 32-bit address and data operating at up to 133 MHz
  - Eight chip selects support eight external slaves
- Integrated DMA controller
  - Four-channel controller
  - All channels accessible by both the local and the remote masters
  - Supports transfers to or from any local memory or I/O port
  - Ability to start and flow control each DMA channel from external 3-pin interface
- Device performance monitor
  - Supports eight 32-bit counters that count the occurrence of selected events
  - Ability to count up to 512 counter-specific events
  - Supports 64 reference events that can be counted on any of the 8 counters
  - Supports duration and quantity threshold counting
  - Burstiness feature that permits counting of burst events with a programmable time between bursts
  - Triggering and chaining capability
  - Ability to generate an interrupt on overflow
- Dual I^2C controllers
  - Two-wire interface
  - Multiple master support
  - Master or slave I^2C mode support
  - On-chip digital filtering rejects spikes on the bus
- Boot sequencer
  - Optionally loads configuration data from serial ROM at reset via the I^2C interface
  - Can be used to initialize configuration registers and/or memory
  - Supports extended I^2C addressing mode
  - Data integrity checked with preamble signature and CRC
- DUART
  - Two 4-wire interfaces (SIN, SOUT, $\overline{\text{RTS}}$, $\overline{\text{CTS}}$)
  - Programming model compatible with the original 16450 UART and the PC16550D
- IEEE 1149.1-compatible, JTAG boundary scan
- Available as 1023 pin Hi-CTE flip chip ceramic ball grid array (FC-CBGA)

NOTE

There is no required order sequence between the individual rails for this item (# 1). However, V_{DD}_PLAT, AV_{DD}_PLAT rails must reach 90% of their recommended value before the rail for Dn_GV_{DD}, and Dn_MV_{REF} (in next step) reaches 10% of their recommended value. AV_{DD} type supplies must be delayed with respect to their source supplies by the RC time constant of the PLL filter circuit described in Section 20.2.1, "PLL Power Supply Filtering."

2. D*n*_GV_{DD}, D*n*_MV_{REF}

NOTE

It is possible to leave the related power supply (D*n*_GV_{DD}, D*n*_MV_{REF}) turned off at reset for a DDR port that will not be used. Note that these power supplies can only be powered up again at reset for functionality to occur on the DDR port.

3. SYSCLK

The recommended order of power down is as follows:

1. D*n*_GV_{DD}, D*n*_MV_{REF}
2. All power rails other than DDR I/O (D*n*_GV_{DD}, D*n*_MV_{REF}).

NOTE

SYSCLK may be powered down simultaneous to either of item # 1 or # 2 in the power down sequence. Beyond this, the power supplies may power down simultaneously if the preservation of DDR*n* memory is not a concern.

See Figure 3 for more details on the Power and Reset Sequencing details.

Table 15 provides the recommended operating conditions for the DDR SDRAM component(s) when D*n*_GV_{DD}(typ) = 2.5 V.

Table 15. DDR SDRAM DC Electrical Characteristics for D*n*_GV_{DD} (typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
I/O supply voltage	D*n*_GV_{DD}	2.375	2.625	V	1
I/O reference voltage	D*n*_MV_{REF}	0.49 × D*n*_GV_{DD}	0.51 × D*n*_GV_{DD}	V	2
I/O termination voltage	V_{TT}	D*n*_MV_{REF} – 0.04	D*n*_MV_{REF} + 0.04	V	3
Input high voltage	V_{IH}	D*n*_MV_{REF} + 0.15	D*n*_GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	D*n*_MV_{REF}– 0.15	V	—
Output leakage current	I_{OZ}	–50	50	μA	4
Output high current (V_{OUT} = 1.95 V)	I_{OH}	–16.2	—	mA	—
Output low current (V_{OUT} = 0.35 V)	I_{OL}	16.2	—	mA	—

Notes:
1. D*n*_GV_{DD} is expected to be within 50 mV of the DRAM D*n*_GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × D*n*_GV_{DD}, and to track D*n*_GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on D*n*_MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to D*n*_MV_{REF}. This rail should track variations in the DC level of D*n*_MV_{REF}.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ D*n*_GV_{DD}.

Table 16 provides the DDR capacitance when D*n*_GV_{DD} (typ)=2.5 V.

Table 16. DDR SDRAM Capacitance for D*n*_GV_{DD} (typ) = 2.5 V

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. D*n*_GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = D*n*_GVDD/2, V_{OUT} (peak-to-peak) = 0.2 V.

Table 17 provides the current draw characteristics for MV_{REF}.

Table 17. Current Draw Characteristics for MV_{REF}

Parameter / Condition	Symbol	Min	Max	Unit	Note
Current draw for MV_{REF}	I_{MVREF}	—	500	μA	1

1. The voltage regulator for MV_{REF} must be able to supply up to 500 μA current.

8 Ethernet: Enhanced Three-Speed Ethernet (eTSEC), MII Management

This section provides the AC and DC electrical characteristics for enhanced three-speed and MII management.

8.1 Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI/RMII Electrical Characteristics

The electrical characteristics specified here apply to all gigabit media independent interface (GMII), media independent interface (MII), ten-bit interface (TBI), reduced gigabit media independent interface (RGMII), reduced ten-bit interface (RTBI), and reduced media independent interface (RMII) signals except management data input/output (MDIO) and management data clock (MDC). The RGMII and RTBI interfaces are defined for 2.5 V, while the GMII and TBI interfaces can be operated at 3.3 or 2.5 V. Whether the GMII or TBI interface is operated at 3.3 or 2.5 V, the timing is compatible with IEEE 802.3. The RGMII and RTBI interfaces follow the Reduced Gigabit Media-Independent Interface (RGMII) Specification Version 1.3 (12/10/2000). The RMII interface follows the RMII Consortium RMII Specification Version 1.2 (3/20/1998). The electrical characteristics for MDIO and MDC are specified in Section 9, "Ethernet Management Interface Electrical Characteristics."

8.1.1 eTSEC DC Electrical Characteristics

All GMII, MII, TBI, RGMII, RMII and RTBI drivers and receivers comply with the DC parametric attributes specified in Table 24 and Table 25. The potential applied to the input of a GMII, MII, TBI, RGMII, RMII or RTBI receiver may exceed the potential of the receiver's power supply (that is, a GMII driver powered from a 3.6-V supply driving V_{OH} into a GMII receiver powered from a 2.5-V supply). Tolerance for dissimilar GMII driver and receiver supply potentials is implicit in these specifications. The RGMII and RTBI signals are based on a 2.5-V CMOS interface voltage as defined by JEDEC EIA/JESD8-5.

Table 24. GMII, MII, RMII, TBI and FIFO DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit	Notes
Supply voltage 3.3 V	LV_{DD} TV_{DD}	3.135	3.465	V	1, 2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –4.0 mA)	V_{OH}	2.40	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 4.0 mA)	V_{OL}	—	0.50	V	—
Input high voltage	V_{IH}	2.0	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	40	μA	1, 2,3

Table 24. GMII, MII, RMII, TBI and FIFO DC Electrical Characteristics (continued)

Parameter	Symbol	Min	Max	Unit	Notes
Input low current (V_{IN} = GND)	I_{IL}	–600	—	μA	3

Notes:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4.
3 The symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

Table 25. GMII, RGMII, RTBI, TBI and FIFO DC Electrical Characteristics

Parameters	Symbol	Min	Max	Unit	Notes
Supply voltage 2.5 V	LV_{DD}/TV_{DD}	2.375	2.625	V	1,2
Output high voltage (LV_{DD}/TV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.00	—	V	—
Output low voltage (LV_{DD}/TV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	—	0.40	V	—
Input high voltage	V_{IH}	1.70	—	V	—
Input low voltage	V_{IL}	—	0.90	V	—
Input high current (V_{IN} = LV_{DD}, V_{IN} = TV_{DD})	I_{IH}	—	10	μA	1, 2,3
Input low current (V_{IN} = GND)	I_{IL}	–15	—	μA	3

Note:

1 LV_{DD} supports eTSECs 1 and 2.
2 TV_{DD} supports eTSECs 3 and 4.
3 Note that the symbol V_{IN}, in this case, represents the LV_{IN} and TV_{IN} symbols referenced in Table 1 and Table 2.

8.2 FIFO, GMII, MII, TBI, RGMII, RMII, and RTBI AC Timing Specifications

The AC timing specifications for FIFO, GMII, MII, TBI, RGMII, RMII and RTBI are presented in this section.

8.2.1 FIFO AC Specifications

The basis for the AC specifications for the eTSEC's FIFO modes is the double data rate RGMII and RTBI specifications, since they have similar performance and are described in a source-synchronous fashion like FIFO modes. However, the FIFO interface provides deliberate skew between the transmitted data and source clock in GMII fashion.

When the eTSEC is configured for FIFO modes, all clocks are supplied from external sources to the relevant eTSEC interface. That is, the transmit clock must be applied to the eTSEC*n*'s TSEC*n*_TX_CLK, while the receive clock must be applied to pin TSEC*n*_RX_CLK. The eTSEC internally uses the transmit

Table 35. RGMII and RTBI AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 2.5 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
Clock period duration [3]	t_{RGT}[5,6]	7.2	8.0	8.8	ns
Duty cycle for 10BASE-T and 100BASE-TX [3, 4]	t_{RGTH}/t_{RGT}[5]	40	50	60	%
Rise time (20%–80%)	t_{RGTR}[5]	—	—	0.75	ns
Fall time (80%–20%)	t_{RGTF}[5]	—	—	0.75	ns

Notes:

1. Note that, in general, the clock reference symbol representation for this section is based on the symbols RGT to represent RGMII and RTBI timing. For example, the subscript of t_{RGT} represents the TBI (T) receive (RX) clock. Note also that the notation for rise (R) and fall (F) times follows the clock symbol that is being represented. For symbols representing skews, the subscript is skew (SK) followed by the clock that is being skewed (RGT).
2. This implies that PC board design will require clocks to be routed such that an additional trace delay of greater than 1.5 ns will be added to the associated clock signal.
3. For 10 and 100 Mbps, t_{RGT} scales to 400 ns ± 40 ns and 40 ns ± 4 ns, respectively.
4. Duty cycle may be stretched/shrunk during speed changes or while transitioning to a received packet's clock domains as long as the minimum duty cycle is not violated and stretching occurs for no more than three t_{RGT} of the lowest speed transitioned between.
5. Guaranteed by characterization
6. ±100 ppm tolerance on RX_CLK frequency

Figure 19 shows the RGMII and RTBI AC timing and multiplexing diagrams.

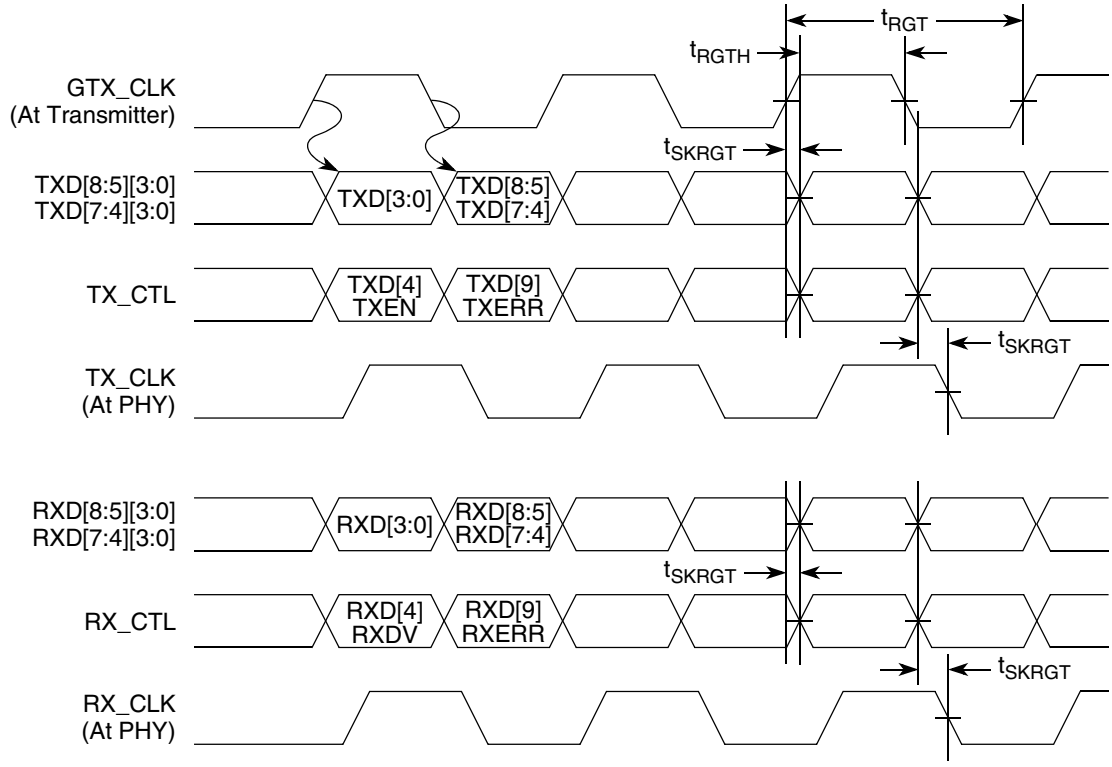

Figure 19. RGMII and RTBI AC Timing and Multiplexing Diagrams

8.2.7 RMII AC Timing Specifications

This section describes the RMII transmit and receive AC timing specifications.

8.2.7.1 RMII Transmit AC Timing Specifications

The RMII transmit AC timing specifications are in Table 36.

Table 36. RMII Transmit AC Timing Specifications

At recommended operating conditions with L/TV_{DD} of 3.3 V ± 5%.

Parameter/Condition	Symbol [1]	Min	Typ	Max	Unit
REF_CLK clock period	t_{RMT}	—	20.0	—	ns
REF_CLK duty cycle	t_{RMTH}/t_{RMT}	35	50	65	%
REF_CLK peak-to-peak jitter	t_{RMTJ}	—	—	250	ps
Rise time REF_CLK (20%–80%)	t_{RMTR}	1.0	—	2.0	ns
Fall time REF_CLK (80%–20%)	t_{RMTF}	1.0	—	2.0	ns
REF_CLK to RMII data TXD[1:0], TX_EN delay	t_{RMTDX}	1.0	—	10.0	ns

Note:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

Figure 20 shows the RMII transmit AC timing diagram.

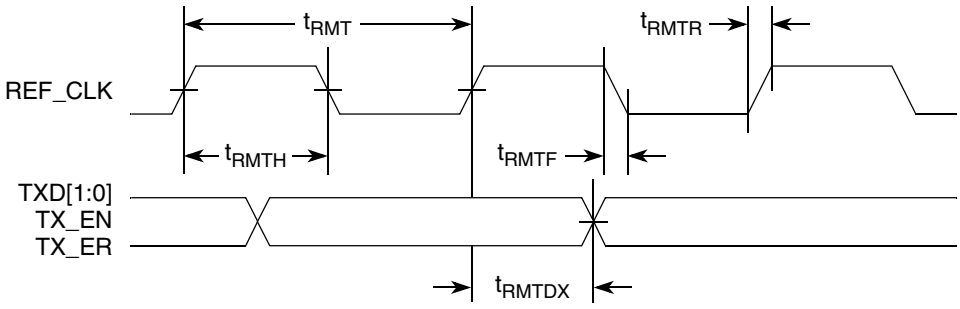

Figure 20. RMII Transmit AC Timing Diagram

10 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8641.

10.1 Local Bus DC Electrical Characteristics

Table 40 provides the DC electrical characteristics for the local bus interface operating at OV_{DD} = 3.3 V DC.

Table 40. Local Bus DC Electrical Characteristics (3.3 V DC)

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = OV_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:
1. Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

10.2 Local Bus AC Electrical Specifications

Table 41 describes the timing parameters of the local bus interface at OV_{DD} = 3.3 V with PLL enabled. For information about the frequency range of local bus see Section 18.1, "Clock Ranges."

Table 41. Local Bus Timing Parameters (OV_{DD} = 3.3 V)m - PLL Enabled

Parameter	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time	t_{LBK}	7.5	—	ns	2
Local Bus Duty Cycle	t_{LBKH}/t_{LBK}	45	55	%	—
LCLK[n] skew to LCLK[m] or LSYNC_OUT	$t_{LBKSKEW}$	—	150	ps	7, 8
Input setup to local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIVKH1}$	1.8	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input setup to local bus clock	$t_{LBIVKH2}$	1.7	—	ns	3, 4
Input hold from local bus clock (except $\overline{\text{LGTA}}$/LUPWAIT)	$t_{LBIXKH1}$	1.0	—	ns	3, 4
$\overline{\text{LGTA}}$/LUPWAIT input hold from local bus clock	$t_{LBIXKH2}$	1.0	—	ns	3, 4
LALE output transition to LAD/LDP output transition (LATCH hold time)	t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	$t_{LBKHOV1}$	—	2.0	ns	—
Local bus clock to data valid for LAD/LDP	$t_{LBKHOV2}$	—	2.2	ns	—
Local bus clock to address valid for LAD	$t_{LBKHOV3}$	—	2.3	ns	—

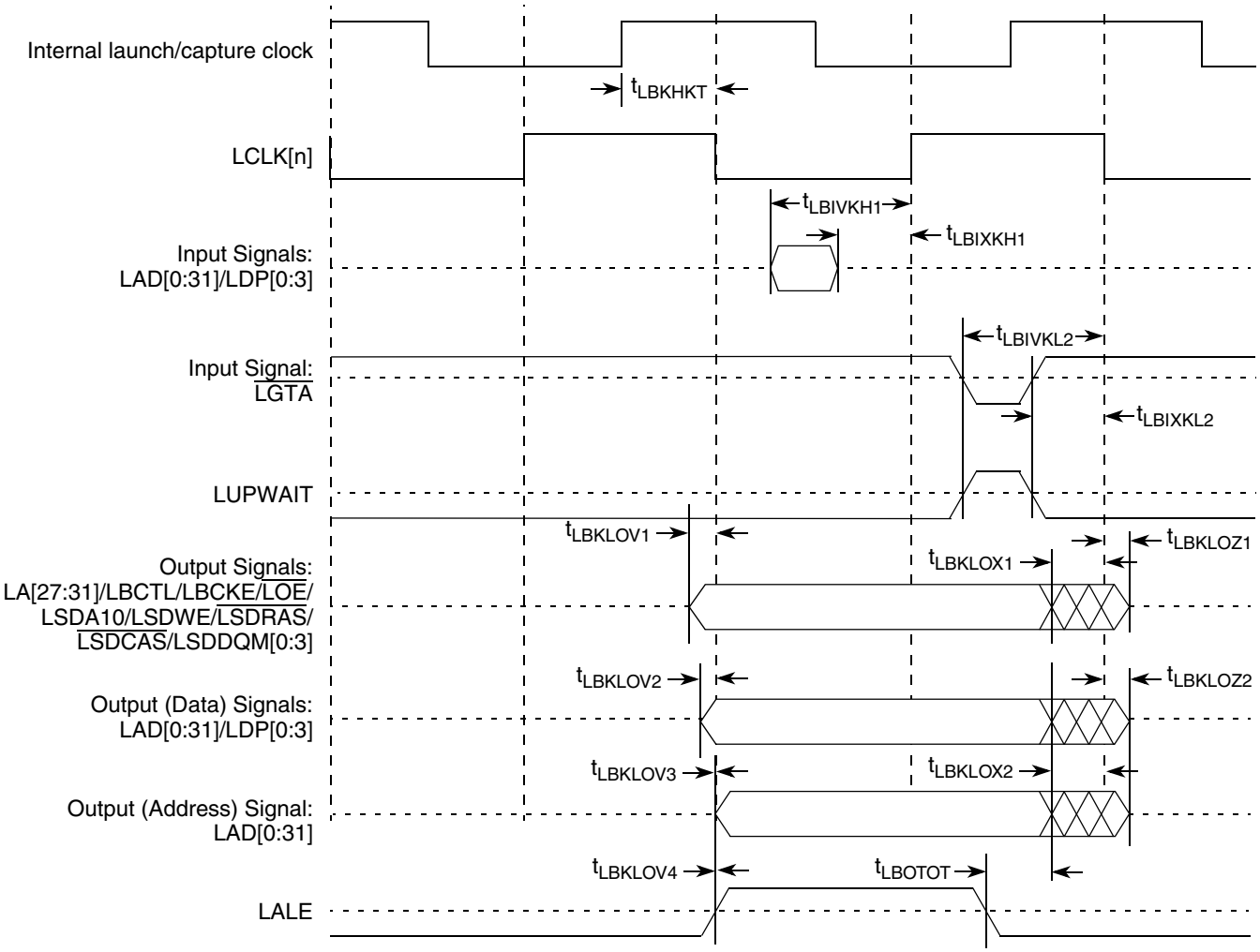

Figure 27. Local Bus Signals (PLL Bypass Mode)

NOTE

In PLL bypass mode, LCLK[n] is the inverted version of the internal clock with the delay of t_{LBKHKT}. In this mode, signals are launched at the rising edge of the internal clock and are captured at falling edge of the internal clock, with the exception of the LGTA/LUPWAIT signal, which is captured at the rising edge of the internal clock.

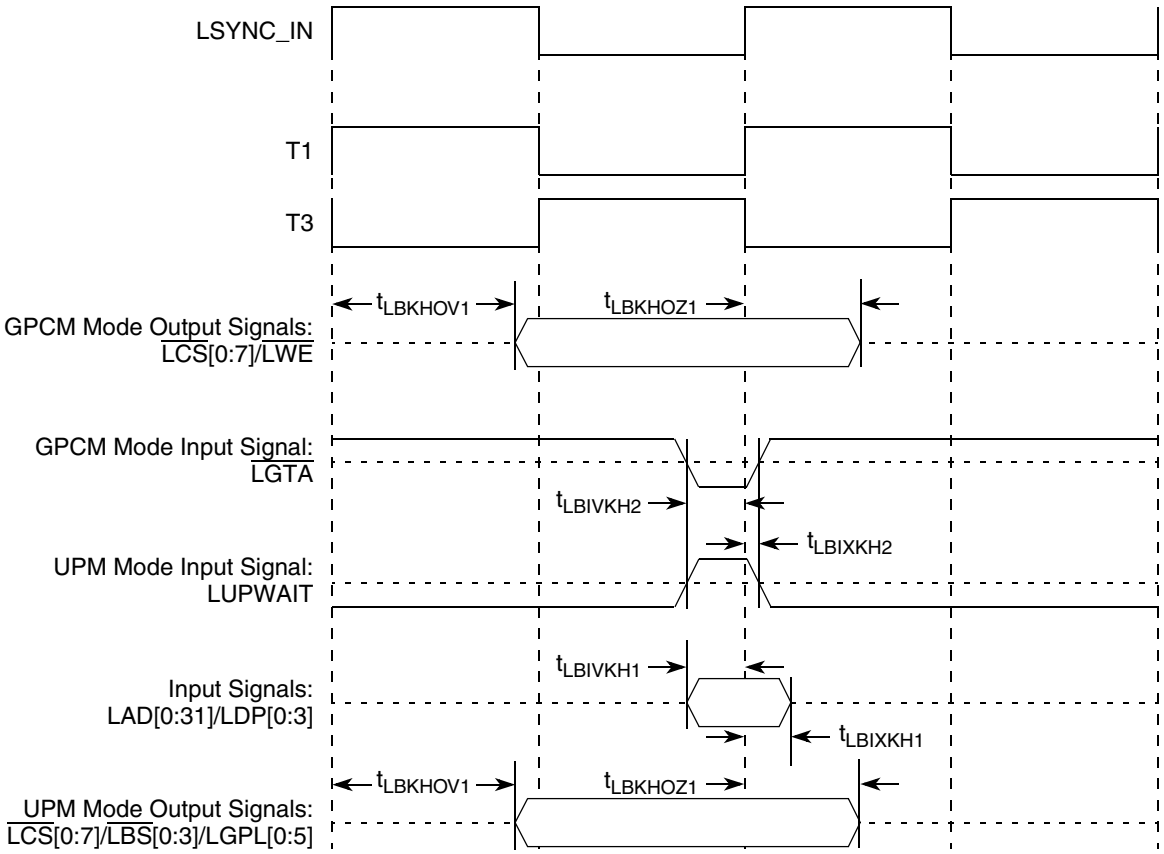

Figure 28. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 2 (clock ratio of 4) (PLL Enabled)

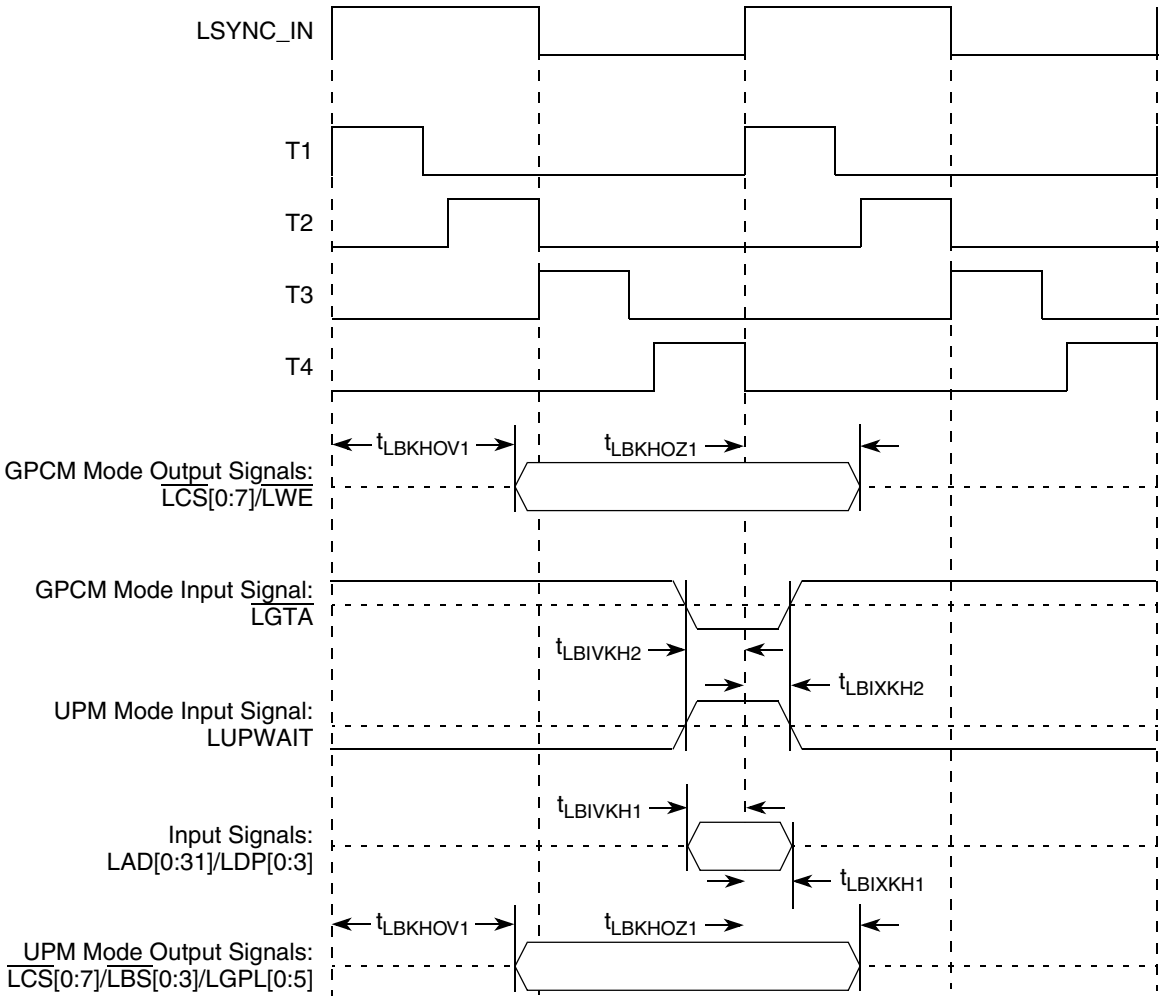

Figure 30. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 or 8 (clock ratio of 8 or 16) (PLL Enabled)

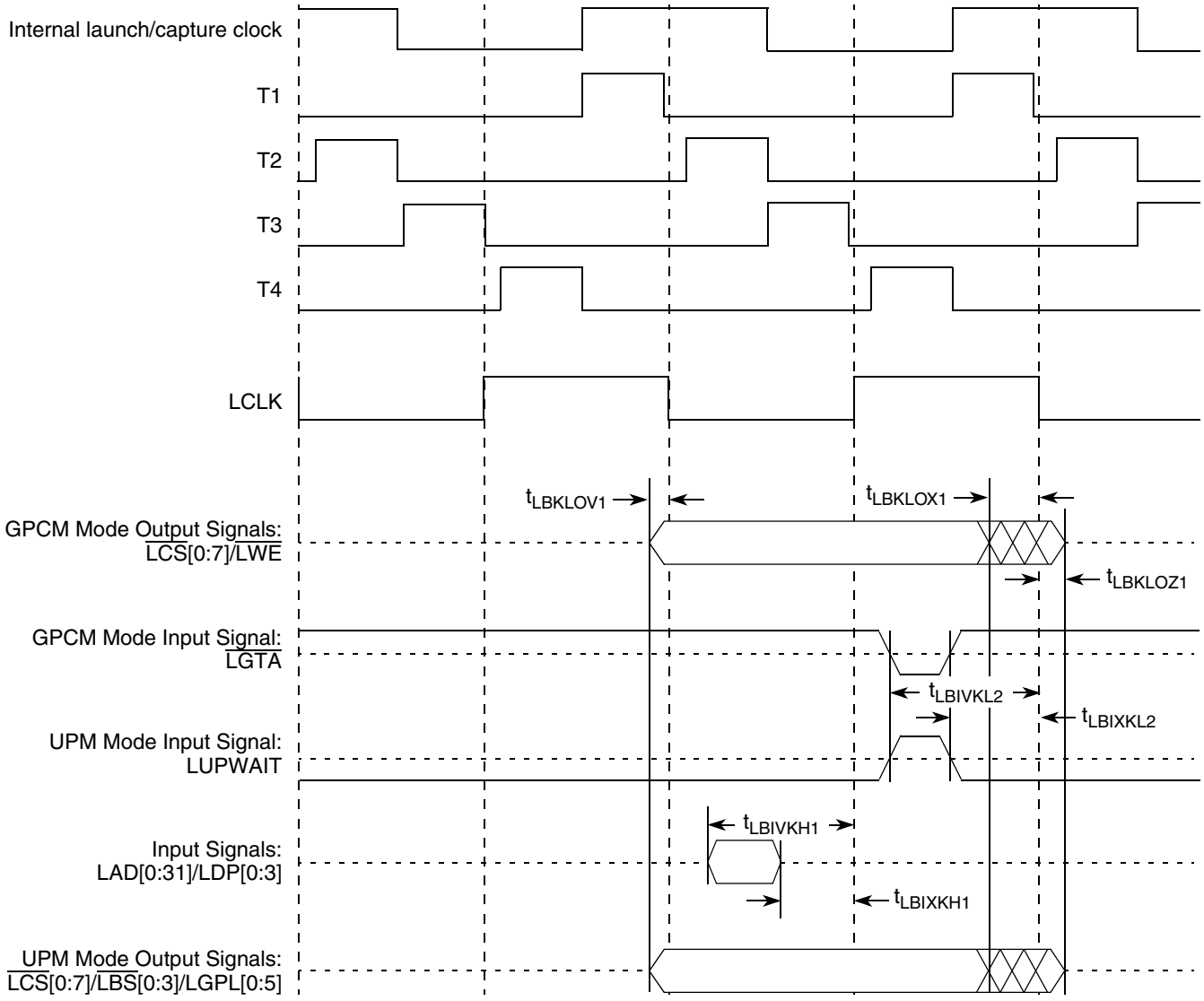

Figure 31. Local Bus Signals, GPCM/UPM Signals for LCRR[CLKDIV] = 4 or 8 (clock ratio of 8 or 16) (PLL Bypass Mode)

Figure 34 provides the $\overline{\text{TRST}}$ timing diagram.

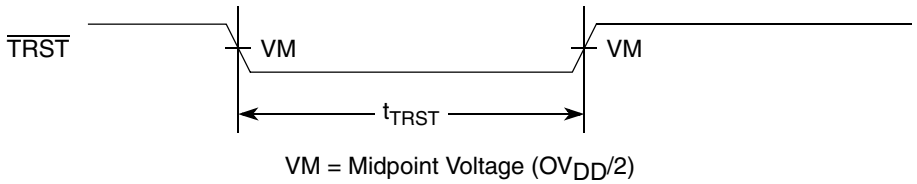

Figure 34. $\overline{\text{TRST}}$ Timing Diagram

Figure 35 provides the boundary-scan timing diagram.

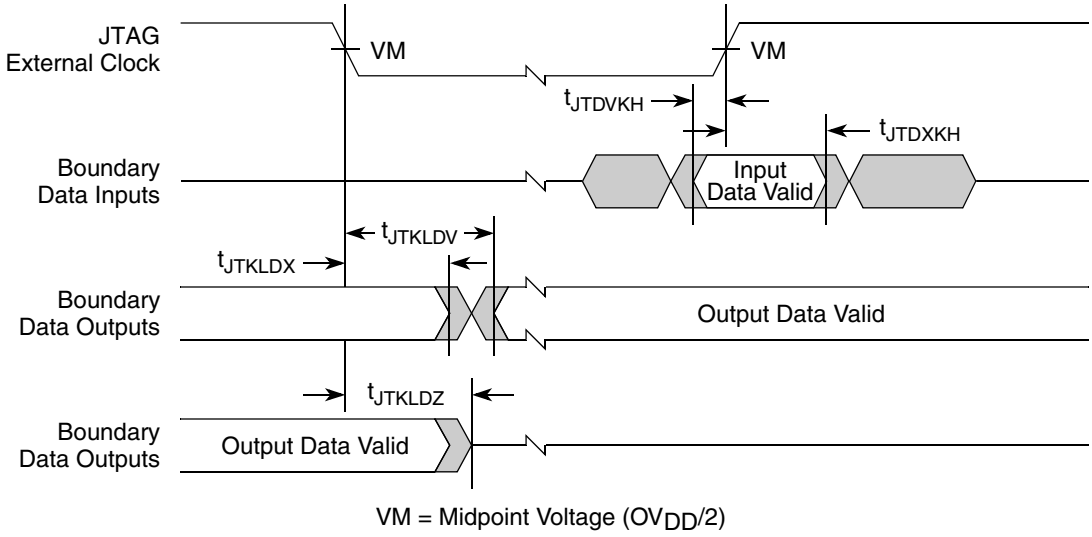

Figure 35. Boundary-Scan Timing Diagram

12 I²C

This section describes the DC and AC electrical characteristics for the I²C interfaces of the MPC8641.

12.1 I²C DC Electrical Characteristics

Table 45 provides the DC electrical characteristics for the I²C interfaces.

Table 45. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	$OV_{DD} + 0.3$	V	—
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	—
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	3

Figure 37 shows the AC timing diagram for the I^2C bus.

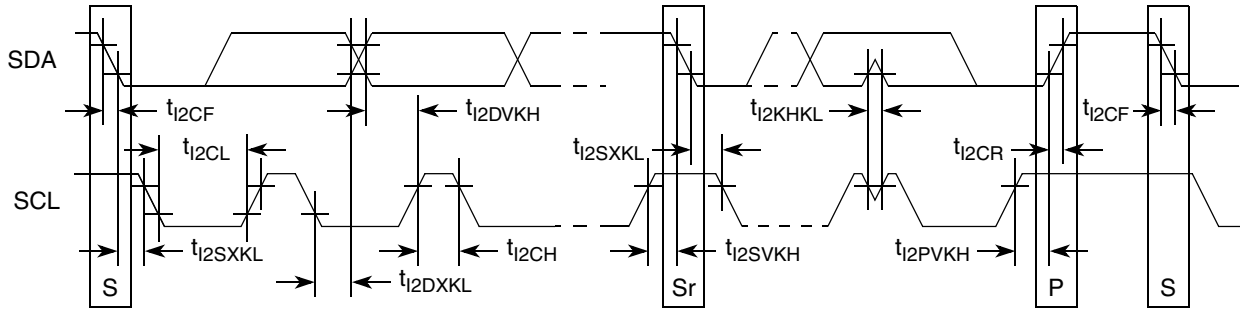

Figure 37. I^2C Bus AC Timing Diagram

13 High-Speed Serial Interfaces (HSSI)

The MPC8641D features two Serializer/Deserializer (SerDes) interfaces to be used for high-speed serial interconnect applications. The SerDes1 interface is dedicated for PCI Express data transfers. The SerDes2 can be used for PCI Express and/or Serial RapidIO data transfers.

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes Reference Clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

13.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 38 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (SD*n*_TX and $\overline{\text{SD}n\text{\_TX}}$) or a receiver input (SD*n*_RX and $\overline{\text{SD}n\text{\_RX}}$). Each signal swings between A Volts and B Volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. **Single-Ended Swing**

   The transmitter output signals and the receiver input signals SD*n*_TX, $\overline{\text{SD}n\text{\_TX}}$, SD*n*_RX and $\overline{\text{SD}n\text{\_RX}}$ each have a peak-to-peak swing of A – B Volts. This is also referred as each signal wire's Single-Ended Swing.

2. **Differential Output Voltage, V_{OD}** (or **Differential Output Swing**):

   The Differential Output Voltage (or Swing) of the transmitter, V_{OD}, is defined as the difference of the two complimentary output voltages: $V_{SDn\_TX} - V_{\overline{SDn\_TX}}$. The V_{OD} value can be either positive or negative.

3. **Differential Input Voltage, V_{ID}** (or **Differential Input Swing**):

13.2.3 Interfacing With Other Differential Signaling Levels

With on-chip termination to SGND, the differential reference clocks inputs are HCSL (High-Speed Current Steering Logic) compatible DC-coupled.

Many other low voltage differential type outputs like LVDS (Low Voltage Differential Signaling) can be used but may need to be AC-coupled due to the limited common mode input range allowed (100 to 400 mV) for DC-coupled connection.

LVPECL outputs can produce signal with too large amplitude and may need to be DC-biased at clock driver output first, then followed with series attenuation resistor to reduce the amplitude, in addition to AC-coupling.

NOTE

Figure 43 to Figure 46 below are for conceptual reference only. Due to the fact that clock driver chip's internal structure, output impedance and termination requirements are different between various clock driver chip manufacturers, it is very possible that the clock circuit reference designs provided by clock driver chip vendor are different from what is shown below. They might also vary from one vendor to the other. Therefore, Freescale Semiconductor can neither provide the optimal clock driver reference circuits, nor guarantee the correctness of the following clock driver connection reference circuits. The system designer is recommended to contact the selected clock driver chip vendor for the optimal reference circuits with the MPC8641D SerDes reference clock receiver requirement provided in this document.

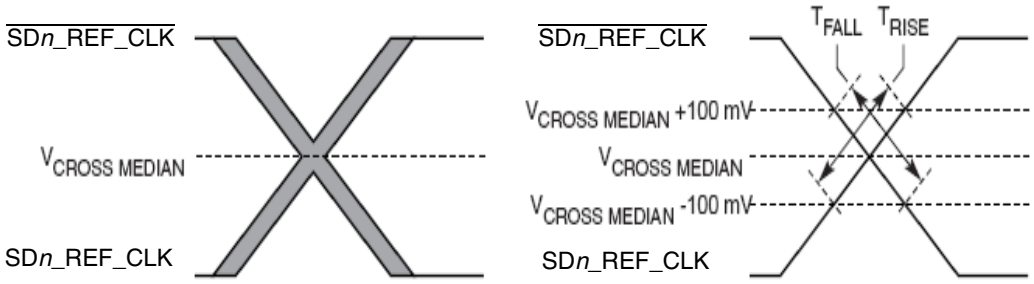

Figure 48. Single-Ended Measurement Points for Rise and Fall Time Matching

The other detailed AC requirements of the SerDes Reference Clocks is defined by each interface protocol based on application usage. Refer to the following sections for detailed information:

- Section 14.2, "AC Requirements for PCI Express SerDes Clocks"
- Section 15.2, "AC Requirements for Serial RapidIO SDn_REF_CLK and SDn_REF_CLK"

13.3 SerDes Transmitter and Receiver Reference Circuits

Figure 49 shows the reference circuits for SerDes data lane's transmitter and receiver.

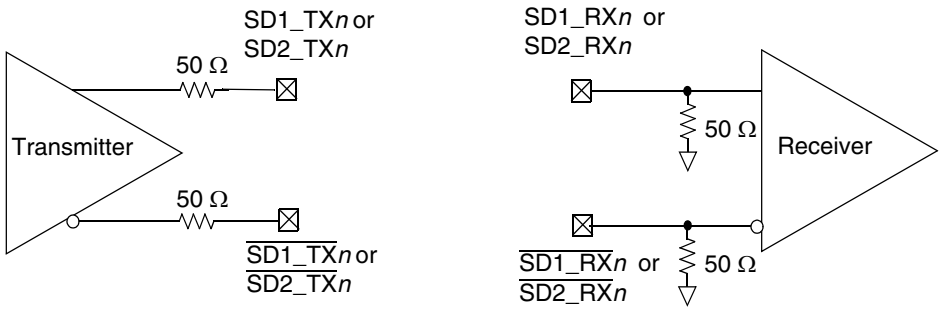

Figure 49. SerDes Transmitter and Receiver Reference Circuits

The DC and AC specification of SerDes data lanes are defined in each interface protocol section below (PCI Express or Serial Rapid IO) in this document based on the application usage:"

- Section 14, "PCI Express"
- Section 15, "Serial RapidIO"

Note that external AC Coupling capacitor is required for the above two serial transmission protocols with the capacitor value defined in specification of each protocol section.

14 PCI Express

This section describes the DC and AC electrical specifications for the PCI Express bus of the MPC8641.

17 Signal Listings

Table 63 provides the pin assignments for the signals. Notes for the signal changes on the single core device (MPC8641) are italicized and prefixed by *"S"*.

Table 63. MPC8641 Signal Reference by Functional Block

Name[1]	Package Pin Number	Pin Type	Power Supply	Notes
DDR Memory Interface 1 Signals[2,3]				
D1_MDQ[0:63]	D15, A14, B12, D12, A15, B15, B13, C13, C11, D11, D9, A8, A12, A11, A9, B9, F11, G12, K11, K12, E10, E9, J11, J10, G8, H10, L9, L7, F10, G9, K9, K8, AC6, AC7, AG8, AH9, AB6, AB8, AE9, AF9, AL8, AM8, AM10, AK11, AH8, AK8, AJ10, AK10, AL12, AJ12, AL14, AM14, AL11, AM11, AM13, AK14, AM15, AJ16, AK18, AL18, AJ15, AL15, AL17, AM17	I/O	$D1\_GV_{DD}$	—
D1_MECC[0:7]	M8, M7, R8, T10, L11, L10, P9, R10	I/O	$D1\_GV_{DD}$	—
D1_MDM[0:8]	C14, A10, G11, H9, AD7, AJ9, AM12, AK16, N10	O	$D1\_GV_{DD}$	—
D1_MDQS[0:8]	A13, C10, H12, J7, AE8, AM9, AK13, AK17, N9	I/O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MDQS}}$[0:8]	D14, B10, H13, J8, AD8, AL9, AJ13, AM16, P10	I/O	$D1\_GV_{DD}$	—
D1_MBA[0:2]	AA8, AA10, T9	O	$D1\_GV_{DD}$	—
D1_MA[0:15]	Y10, W8, W9, V7, V8, U6, V10, U9, U7, U10, Y9, T6, T8, AE12, R7, P6	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MWE}}$	AB11	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MRAS}}$	AB12	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCAS}}$	AC10	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCS}}$[0:3]	AB9, AD10, AC12, AD11	O	$D1\_GV_{DD}$	—
D1_MCKE[0:3]	P7, M10, N8, M11	O	$D1\_GV_{DD}$	23
D1_MCK[0:5]	W6, E13, AH11, Y7, F14, AG10	O	$D1\_GV_{DD}$	—
$\overline{\text{D1\_MCK}}$[0:5]	Y6, E12, AH12, AA7, F13, AG11	O	$D1\_GV_{DD}$	—
D1_MODT[0:3]	AC9, AF12, AE11, AF10	O	$D1\_GV_{DD}$	—
D1_MDIC[0:1]	E15, G14	IO	$D1\_GV_{DD}$	27
$D1\_MV_{REF}$	AM18	DDR Port 1 reference voltage	$D1\_GV_{DD}$ /2	3
DDR Memory Interface 2 Signals[2,3]				

Another useful equation is:

$$V_H - V_L = n\frac{KT}{q}\left[ln\frac{I_H}{I_L}\right]$$

Where:

I_{fw} = Forward current
I_s = Saturation current
V_d = Voltage at diode
V_f = Voltage forward biased
V_H = Diode voltage while I_H is flowing
V_L = Diode voltage while I_L is flowing
I_H = Larger diode bias current
I_L = Smaller diode bias current
q = Charge of electron (1.6×10^{-19} C)
n = Ideality factor (normally 1.0)
K = Boltzman's constant (1.38×10^{-23} Joules/K)
T = Temperature (Kelvins)

The ratio of I_H to I_L is usually selected to be 10:1. The above simplifies to the following:

$$V_H - V_L = 1.986 \times 10^{-4} \times nT$$

Solving for T, the equation becomes:

$$nT = \frac{V_H - V_L}{1.986 \times 10^{-4}}$$

The following pins must be connected to GND:

- SD*n*_RX[7:0]
- $\overline{\text{SD}n\text{\_RX}}$[7:0]
- SD*n*_REF_CLK
- $\overline{\text{SD}n\text{\_REF\_CLK}}$

NOTE

It is recommended to power down the unused lane through SRDS1CR1[0:7] register (offset = 0xE_0F08) and SRDS2CR1[0:7] register (offset = 0xE_0F44.) (This prevents the oscillations and holds the receiver output in a fixed state.) that maps to SERDES lane 0 to lane 7 accordingly.

For other directions on reserved or no-connects pins see Section 17, "Signal Listings."

20.6 Pull-Up and Pull-Down Resistor Requirements

The MPC8641 requires weak pull-up resistors (2–10 kΩ is recommended) on all open drain type pins.

The following pins must NOT be pulled down during power-on reset: TSEC4_TXD[4], LGPL0/LSDA10, LGPL1/$\overline{\text{LSDWE}}$, TRIG_OUT/READY, and D1_MSRCID[2].

The following are factory test pins and require strong pull up resistors (100 Ω –1 kΩ) to OVDD

LSSD_MODE, TEST_MODE[0:3].The following pins require weak pull up resistors (2–10 kΩ) to their specific power supplies: LCS[0:4], LCS[5]/DMA_DREQ2, LCS[6]/DMA_DACK[2], LCS[7]/DMA_DDONE[2], IRQ_OUT, IIC1_SDA, IIC1_SCL, IIC2_SDA, IIC2_SCL, and CKSTP_OUT.

The following pins should be pulled to ground with a 100-Ω resistor: SD1_IMP_CAL_TX, SD2_IMP_CAL_TX. The following pins should be pulled to ground with a 200-Ω resistor: SD1_IMP_CAL_RX, SD2_IMP_CAL_RX.

TSEC*n*_TX_EN signals require an external 4.7-kΩ pull down resistor to prevent PHY from seeing a valid Transmit Enable before it is actively driven.

When the platform frequency is 400 MHz, TSEC1_TXD[1] must be pulled down at reset.

TSEC2_TXD[4] and TSEC2_TX_ER pins function as cfg_dram_type[0 or 1] at reset and MUST BE VALID BEFORE HRESET ASSERTION when coming out of device sleep mode.

20.6.1 Special instructions for Single Core device

The mechanical drawing for the single core device does not have all the solder balls that exist on the single core device. This includes all the balls for VDD_Core1 and $\text{SENSEV}_{\text{DD}}$_Core1 which exist on the package for the dual core device, but not on the single core package. A solder ball is present for $\text{SENSEV}_{\text{SS}}$_Core1 and needs to be connected to ground with a weak (2-10 kΩ) pull down resistor. Likewise, AV_{DD}_Core1 needs to be pulled to ground as shown in Figure 64.

The mechanical drawing for the single core device is located in Section 16.2, "Mechanical Dimensions of the MPC8641 FC-CBGA."

The COP interface has a standard header, shown in Figure 67, for connection to the target system, and is based on the 0.025" square-post, 0.100" centered header assembly (often called a Berg header). The connector typically has pin 14 removed as a connector key.

The COP header adds many benefits such as breakpoints, watchpoints, register and memory examination/modification, and other standard debugger features. An inexpensive option can be to leave the COP header unpopulated until needed.

There is no standardized way to number the COP header shown in Figure 67; consequently, many different pin numbers have been observed from emulator vendors. Some are numbered top-to-bottom then left-to-right, while others use left-to-right then top-to-bottom, while still others number the pins counter clockwise from pin 1 (as with an IC). Regardless of the numbering, the signal placement recommended in Figure 67 is common to all known emulators.

For a multi-processor non-daisy chain configuration, Figure 68, can be duplicated for each processor. The recommended daisy chain configuration is shown in Figure 69. Please consult with your tool vendor to determine which configuration is supported by their emulator.

20.9.1 Termination of Unused Signals

If the JTAG interface and COP header will not be used, Freescale recommends the following connections:

- $\overline{\text{TRST}}$ should be tied to $\overline{\text{HRESET}}$ through a 0 kΩ isolation resistor so that it is asserted when the system reset signal ($\overline{\text{HRESET}}$) is asserted, ensuring that the JTAG scan chain is initialized during the power-on reset flow. Freescale recommends that the COP header be designed into the system as shown in Figure 68. If this is not possible, the isolation resistor will allow future access to $\overline{\text{TRST}}$ in case a JTAG interface may need to be wired onto the system in future debug situations.
- Tie TCK to OV_{DD} through a 10 kΩ resistor. This will prevent TCK from changing state and reading incorrect data into the device.
- No connection is required for TDI, TMS, or TDO.

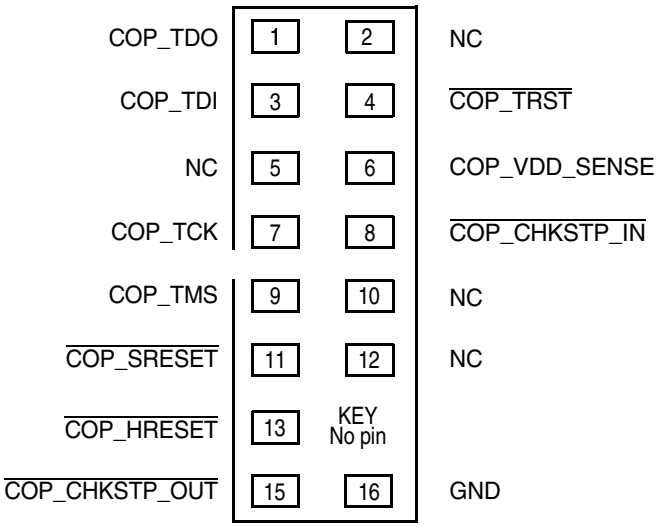

Figure 67. COP Connector Physical Pinout